

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. ASMMC.057AUS	APPLICATION NO. 10/810,415
	APPLICANT Leinikka et al..	
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EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	101.	Martensson et al., "Atomic Layer Epitaxy of Copper and Tantalum," <u>Chemical Vapor Deposition</u> , Vol. 3, No. 1, pp. 45-50, (1997)
	102.	Martensson et al., "CU(THD) ₂ As Copper Source in Atomic Layer Epitaxy," <u>Electrochemical Society Proceedings</u> , Vol. 97-25, pp. 1529-1536, (1997).
	103.	Martensson, "Use of atomic layer epitaxy for fabrication of Si/TiN/Cu structures," <u>J. Vac. Sci. Technol. B</u> , Vol. 17, No. 5, pp. 2122-2128, (Sept./Oct. 1999)
	104.	Min, Jae-Sik, Young Woong Son, Won-Gu Kang, Soung-Soon Chun, and Sang-Won Kang, "Atomic Layer Deposition of TiN Films by Alternate Supply of Tetrakis (ethylmethylamino)-Titanium and Ammonia," <u>Jpn. J. Appl. Phys.</u> , Vol. 37, pp. 4999-5004, (1998).
	105.	Min, Jae-Sik, Young-Woong Son, Won-Gu Kang, and Sang-Won Kang, "Atomic Layer Deposition of TiN Thin Films by Sequential Introduction of Ti Precursor and HN ₃ ," <u>Mat. Res. Soc. Symp. Proc.</u> , Vol. 514, pp. 337-342, (1998).
	106.	Nakajima, Tsuyoshi and Toru Shirasaki, "Chemical Vapor Deposition of Tungsten Carbide, Molybdenum Carbide Nitride, and Molybdenum Nitride Films," <u>J. Electrochem. Soc.</u> , Vol. 144, No. 6, pp. 2096-2100, (June 1997)
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	108.	Ritala et al., "Atomic layer epitaxy growth of TiN thin films," <u>J. Electrochem. Soc.</u> , 142(8):2731-2737 (1995)
	109.	Ritala, Mikko, Markku Leskelä, Eero Rauhala, and Janne Jokinen, "Atomic Layer Epitaxy Growth of TiN Thin Films from TiI ₄ and NH ₃ ," <u>J. Electrochem. Soc.</u> , Vol. 145, No. 8, pp. 2914-2920, (August 1998)
	110.	Ritala et al., "Effects of intermediate zinc pulses on properties of TiN and NbN films deposited by atomic layer epitaxy," <u>Appl. Surf. Sci.</u> , 120:199-212 (1997).
	111.	Ritala et al., "Perfectly conformal TiN and Al ₂ O ₃ films deposited by atomic layer deposition," <u>Chem. Vapor Deposition</u> , 5:7-9 (1999).
	112.	Ryu et al., "Barriers for copper interconnections," <u>Solid State Technology</u> , April, 53 (1999).
	113.	Sherman et al., "Plasma enhanced atomic layer deposition of Ta for diffusion barrier applications," AVS 46 th International Symposium, Paper TF-TuM5 (abstract), (October 26, 1999), Seattle, WA.
	114.	Yang et al., "Atomic Layer Deposition of Tungsten Film from WF ₆ /B ₂ H ₆ : Nucleation Layer for Advanced Semiconductor Devices," Advanced Metallization Conference 2001 (AMC 2001), Conference Proceedings ULSI XVII@2002 Materials Research Society, pp. 655-660.

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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /AC/ (03/14/2008)

EXAMINER /Alonzo Chambliss/ (03/14/2008)	DATE CONSIDERED
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